FIG. 1

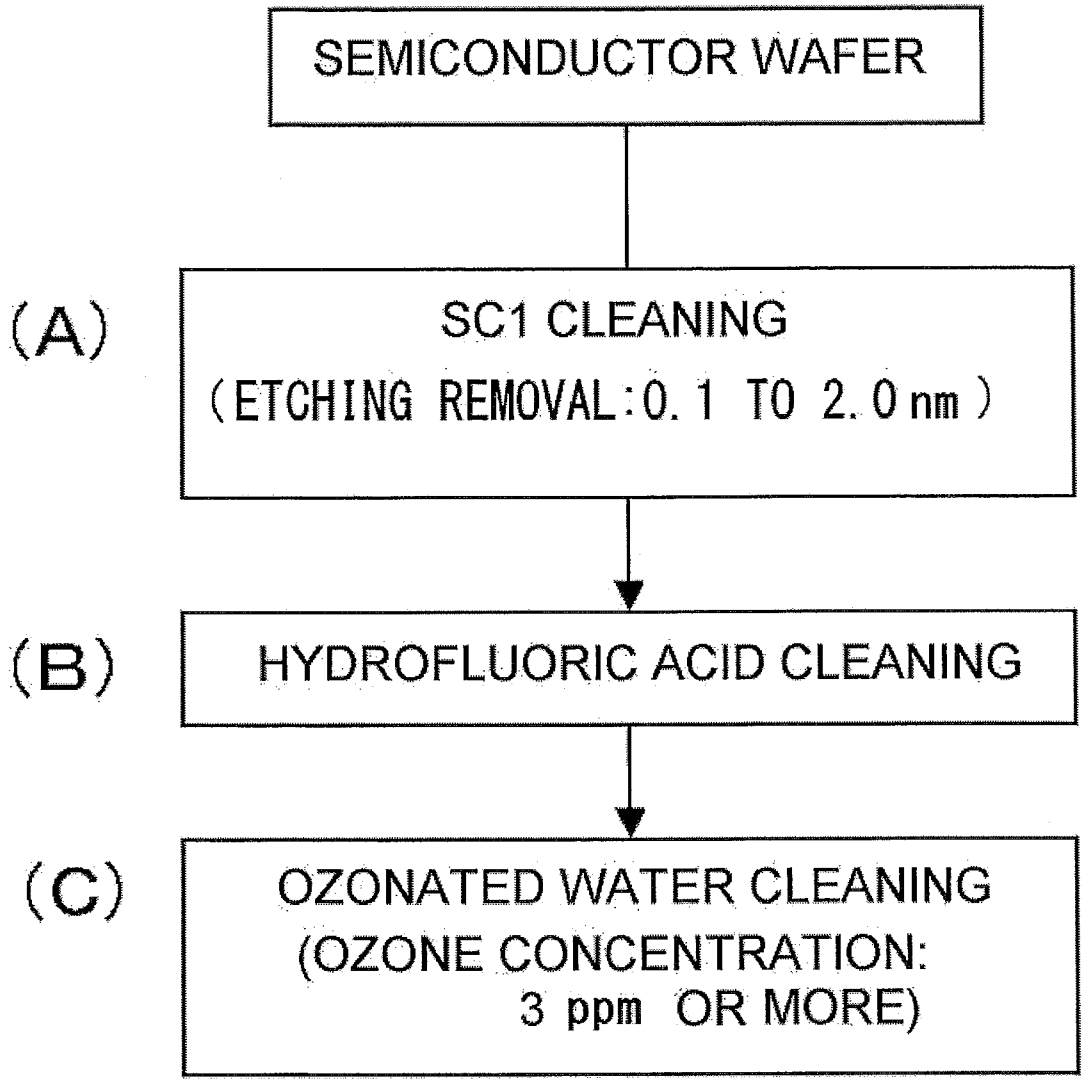

SEMICONDUCTOR WAFER
(A)
SC1 CLEANING
(ETCHING REMOVAL:0.1 TO 2.0 nm)
(B)
HYDROFLUORIC ACID CLEANING
(C)
OZONATED WATER CLEANING
(OZONE CONCENTRATION:
3 ppm OR MORE)

FIG. 2

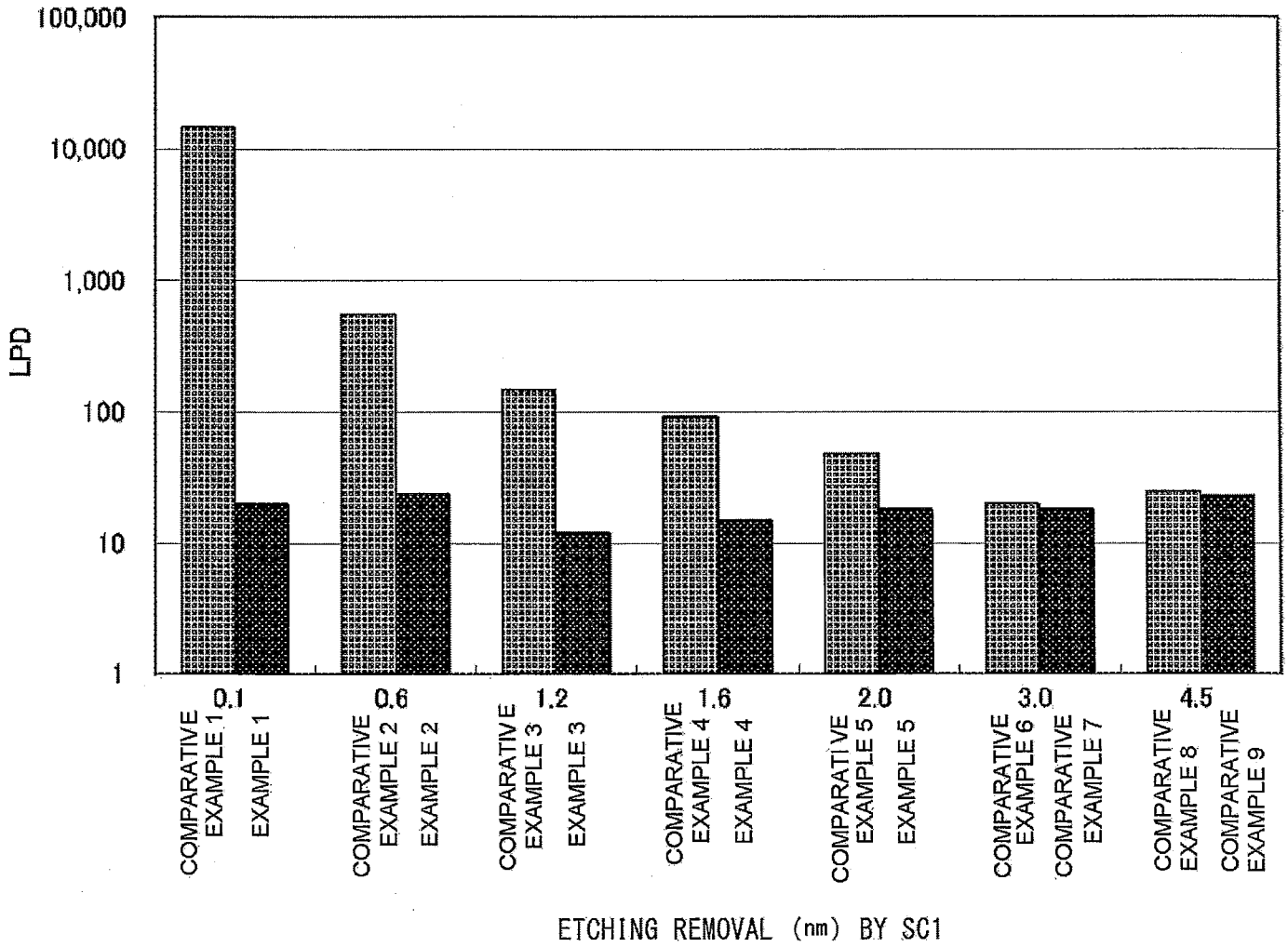

100,000
10,000
1,000
100
10
1
LPD
0.1
COMPARATIVE EXAMPLE 1
EXAMPLE 1
0.6
COMPARATIVE EXAMPLE 2
EXAMPLE 2
1.2
COMPARATIVE EXAMPLE 3
EXAMPLE 3
1.6
COMPARATIVE EXAMPLE 4
EXAMPLE 4
2.0
COMPARATIVE EXAMPLE 5
EXAMPLE 5
3.0
COMPARATIVE EXAMPLE 6
COMPARATIVE EXAMPLE 7
4.5
COMPARATIVE EXAMPLE 8
COMPARATIVE EXAMPLE 9
ETCHING REMOVAL (nm) BY SC1

FIG. 3

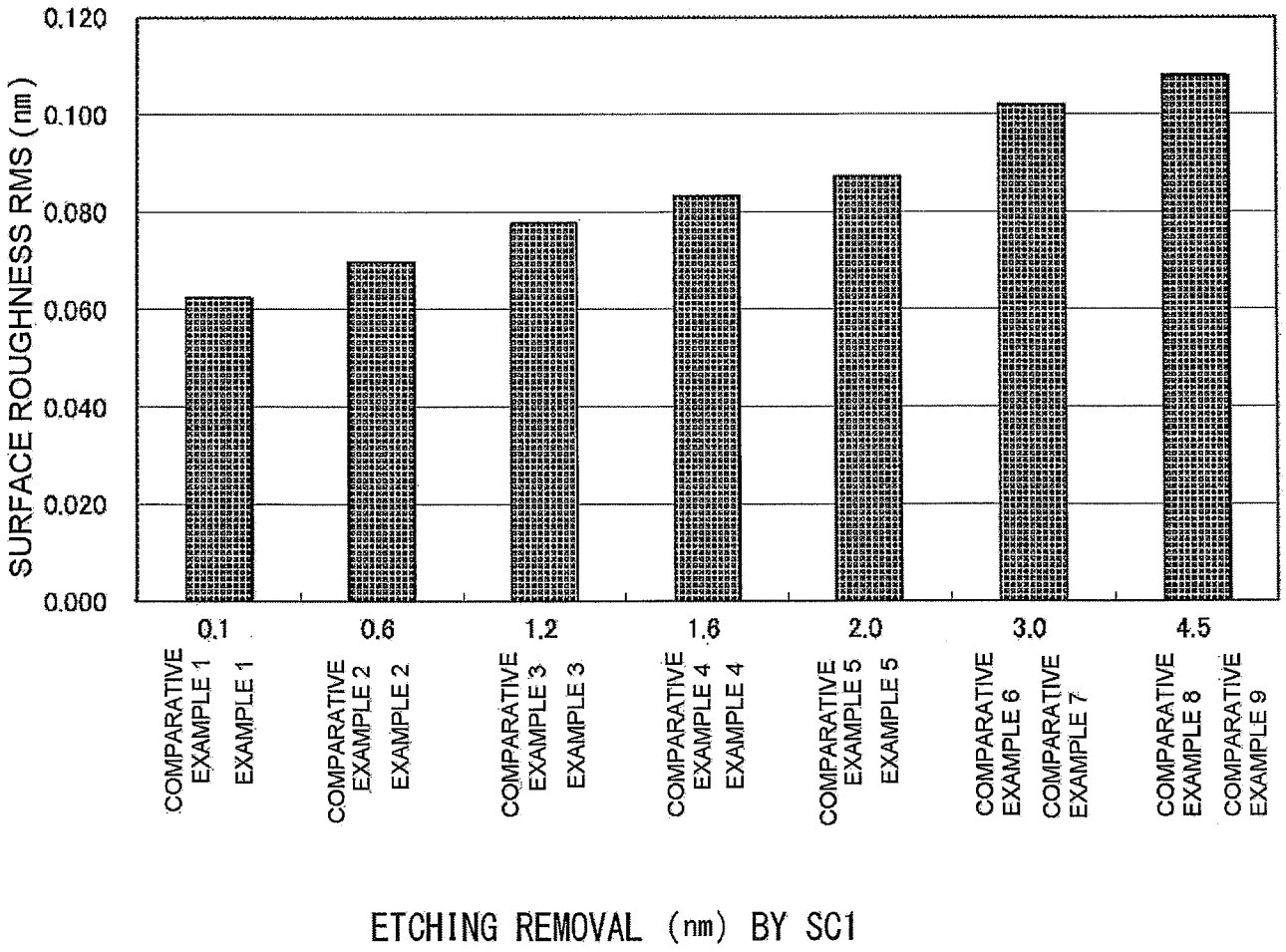
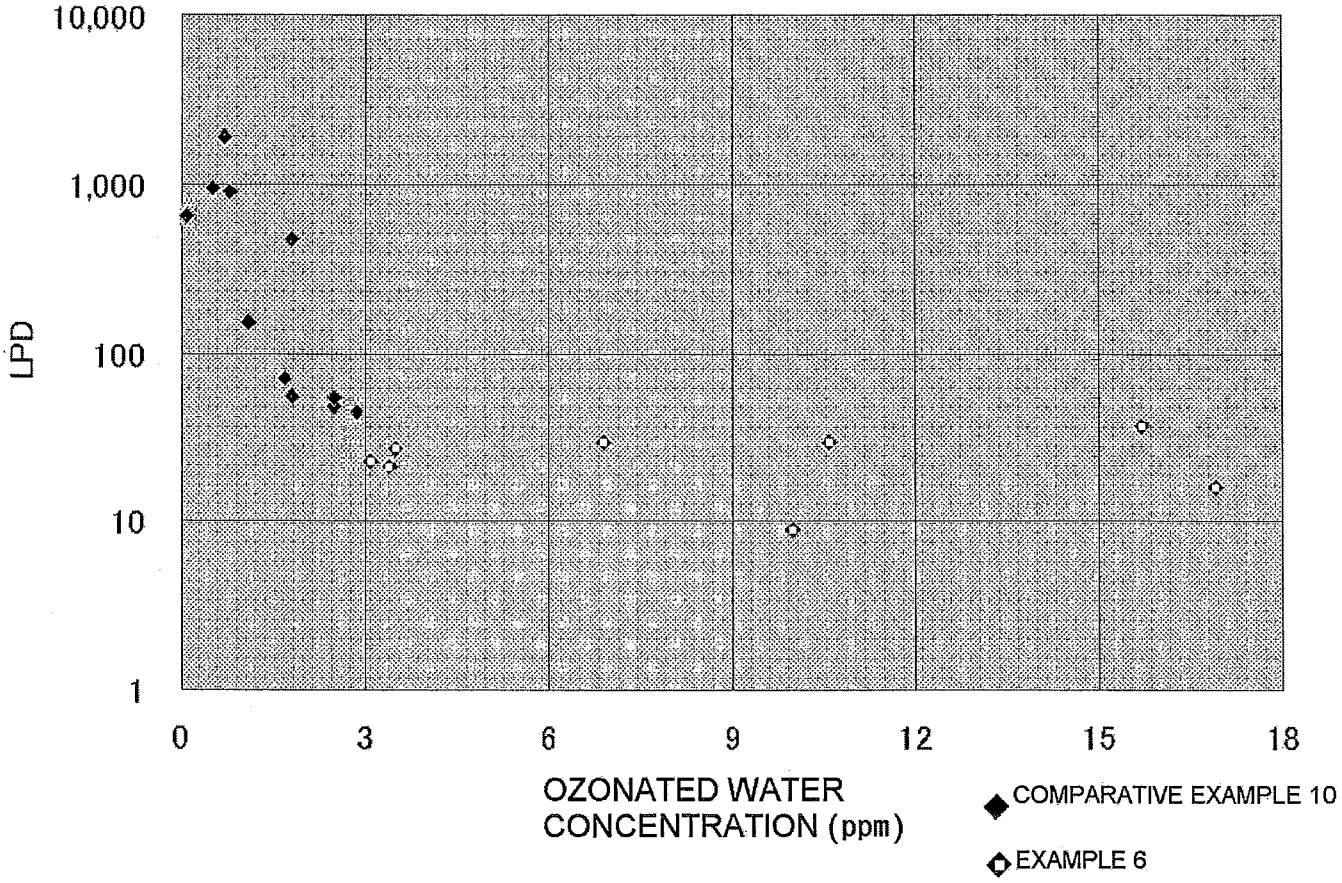

SURFACE ROUGHNESS RMS (nm)
0.120
0.100
0.080
0.060
0.040
0.020
0.000
0.1
0.6
1.2
1.6
2.0
3.0
4.5
COMPARATIVE EXAMPLE 1
EXAMPLE 1
COMPARATIVE EXAMPLE 2
EXAMPLE 2
COMPARATIVE EXAMPLE 3
EXAMPLE 3
COMPARATIVE EXAMPLE 4
EXAMPLE 4
COMPARATIVE EXAMPLE 5
EXAMPLE 5
COMPARATIVE EXAMPLE 6
COMPARATIVE EXAMPLE 7
COMPARATIVE EXAMPLE 8
COMPARATIVE EXAMPLE 9
ETCHING REMOVAL (nm) BY SC1

FIG. 4


10,000
1,000
100
10
1
LPD
0
3
6
9
12
15
18
OZONATED WATER CONCENTRATION (ppm)
COMPARATIVE EXAMPLE 10
EXAMPLE 6